



P-CHANNEL ENHANCEMENT MODE MOSFETS

Part No.	V <sub>(BR)DSS</sub> Volts Min	V <sub>(BR)CSS</sub> Volts Min	V <sub>(BR)DC</sub> Volts Min	Power Dis. 25°C Amb mW Max	I <sub>DSS</sub> nA Typ	I <sub>SSSF</sub> nA Typ	I <sub>D(on)</sub> mA Typ	V <sub>GS(th)</sub> Volts Min/Max	r <sub>DS(on)</sub> Ohms Typ	Y <sub>Fs</sub> μmho Typ	C <sub>iss</sub> pF Typ	C <sub>rss</sub> pF Typ	Case P.18 P.19	Lead Con- fig. P.20
* MEM 511	-30	-30	-30	225	-0.5	-0.05*	-6	-3.0/-6.0	150	2,500	3.5	2.5	4	1
* MEM 511C	-25	-25	-25	175	-3.0	-0.05*	-6	-3.0/-6.0	150	2,500	4.0	4.0	4	1
* MEM 517	-30	-25	-25	600	-0.8	-0.15*	-60	-2.5/-5.0	35	12,000	10.0	10.0	2	1
* MEM 517A	-30	-25	-25	600	-0.8	-0.15*	-60	-2.5/-5.0	35	12,000	10.0	10.0	1	6
* MEM 517B	-30	-25	-25	300	-0.8	-0.15*	-60	-2.5/-5.0	35	12,000	10.0	10.0	4	1
#* MEM 517C	-25	-25	-25	450	-3.5	-0.15*	-50	-2.5/-5.0	35	12,000	10.0	10.0	2	1
MEM 520	-30	-40	-40	225	-0.5	-0.03 pA	-5	-3.0/-6.0	150	2,500	3.0	2.5	4	1
MEM 520C	-25	-25	-25	175	-3.0	-0.1 pA	-5	-3.0/-6.0	150	2,500	3.0	2.5	4	1
* MEM 556	-50	-50	-50	100	-0.1	-0.1*	-7	-3.0/-6.0	700	950	0.3	0.3	4	1
#* MEM 556C	-45	-45	-45	100	-0.3	-0.3*	-7	-3.0/-6.0	700	950	0.4	0.4	4	1
* MEM 560	-35	-35	-35	300	-1.0	-0.1*	-20	-1.5/-3.0	100	3,500	7.5	1.5	4	1
* MEM 560C	-30	-30	-30	200	-2.0	-0.2*	-15	-1.0/-3.5	175	3,500	8.0	2.0	4	1
MEM 561	-30	-50	-40	225	-1.0	-0.05 pA	-20	-1.5/-3.0	100	3,500	7.5	3.0	4	1
#* MEM 561C	-25	-40	-30	225	-0.5	-0.5 pA	-30	-1.5/-3.0	150	3,500	7.5	3.0	4	1
#* MEM 575	-25	-25	-25	300	-1.0	-0.2*	-200	-1.0/-3.5	13	15,000	45.0	15.0	4	1
* MEM 803	-20	-20	-20	150	-3.0	-0.2*	-5	-2.0/-6.5	200	1,000	4.5	4.0	4	1
MEM 804	-30	-40	-35	225	-2.0	-0.1 pA	-12	-1.5/-3.0	175	3,000	7.0	3.0	4	1
MEM 806	-40	-40	-40	300	-1.0	-0.1 pA	-7	-2.0/-5.5	150	2,800	4.5	1.0	4	1
MEM 806A	-40	-40	-40	300	-0.1	-0.05 pA	-7	-2.0/-5.5	150	2,800	4.5	1.0	4	1
#* MEM 807	-40	-40	-40	300	-0.5	-0.1*	-7	-2.0/-5.5	150	2,800	4.5	1.0	4	1
* MEM 807A	-40	-40	-40	300	-0.05	-0.2*	-7	-2.0/-5.5	150	2,800	4.5	1.0	4	1
* MEM 814	-35	-35	-35	300	-1.0	-0.1*	-20	-1.5/-3.0	80	3,500	6.0	1.0	4	1
#* MEM 816	-30	-30	-30	200	-5.0	-0.2*	-20	-2.0/-5.0	150	3,000	6.0	3.5	10	3
#* MEM 817	-45	-200	-45	225	-0.5	-0.01 pA	-12	-2.5/-5.5	—	2,000	3.5	1.2	4	1
2N 3608	-25	-25	-25	350	-1.0	-0.1 pA	-4	-4.0/-6.0	150	2,000	4.0	3.5	2	1
2N 4065	-30	-25	-25	225	-0.1	-0.5 pA	-6	-3.0/-6.0	500	2,000	2.5	0.3	4	1
2N 4120	-30	-40	-40	350	-0.1	-0.1	-6.5	-3.0/-6.0	600	900	3.0	2.5	4	1
2N 4352	-25	-15	-25	300	-3.0	-5.0 pA	-4	-1.0/-5.0	150	2,500	2.5	0.7	4	3
* 2N 4353	-30	-30	-30	250	-0.5	-0.1*	-4	-3.0/-5.0	125	3,000	6.0	3.0	4	1
3N 145	-30	-50	-50	250	-1.0	-1.0	-5	-2.0/-6.0	600	—	0.1	0.5	4	1
3N 146	-30	-50	-50	250	-1.0	-0.1	-5	-2.0/-6.0	600	—	0.1	0.5	4	1
3N 155	-35	-50	-50	250	-0.4	-5.0	-7	-1.5/-3.2	250	—	2.5	0.7	4	3
3N 155A	-35	-50	-50	250	-0.1	-5.0	-7	-1.5/-3.2	150	—	2.5	0.7	4	3
3N 156	-35	-50	-50	250	-0.5	-5.0	-7	-3.0/-5.0	300	—	2.5	0.7	4	3
3N 156A	-35	-50	-50	250	-0.1	-5.0	-7	-3.0/-5.0	150	—	2.5	0.7	4	3
3N 157	-35	-50	-50	250	-0.5	-5.0	-4	-1.5/-3.2	—	2,500	2.5	0.7	4	3
3N 157A	-50	-50	-50	250	-0.1	-5.0	-4	-1.5/-3.2	—	2,500	2.5	0.7	4	3
3N 158	-35	-50	-50	250	-0.5	-5.0	-4	-3.0/-5.0	—	2,500	2.5	0.7	4	3
3N 158A	-50	-50	-50	250	-0.1	-5.0	-4	-3.0/-5.0	—	2,500	2.5	0.7	4	3
3N 160	-25	-25	-25	250	-5.0	-5.0 pA	-60	-1.5/-5.0	75	4,500	5.0	2.0	4	1
3N 161	-25	-25	-25	250	-5.0	-0.05	-60	-1.5/-5.0	75	4,500	5.0	2.0	4	1
* 3N 162	-30	-25	-25	600	-10	-0.2*	-50	-2.5/-5.0	40	13,000	10.0	5.0	2	1
3N 163	-40	-40	-40	375	-0.1	-0.01	-20 mA	-2.0/-5.0	200	3,000	2.0	0.7	4	1
3N 164	-30	-30	-30	375	-0.2	-0.01	-20 mA	-2.0/-5.0	250	3,000	2.0	0.7	4	1
3N 167	-30	-30	-30	225	-0.03	-0.07	-200 mA	-2.0/-6.0	17	—	3.5	12.0	4	1
3N 168	-25	-25	-25	225	-0.08	-0.4	-100 mA	-2.0/-6.0	35	—	3.5	12.0	4	1
3N 172	-40	-40	-40	375	-0.3	-0.1	-20	-2.0/-5.0	200	3,000	3.0	0.8	4	1
3N 173	-40	-40	-40	375	-8.0	-0.3	-20	-2.0/-5.0	300	3,000	3.0	0.8	4	1
3N 174	-30	-30	-30	360	-3.0	-2.0 pA	-10	-2.0/-6.0	800	2,000	3.5	0.6	4	1
* 3N 178	-75	-45	-75	100	-0.1	-0.15*	-6	-4.5/-5.5	750	1,000	0.3	0.2	4	1
* 3N 179	-60	-45	-60	100	-0.3	-0.2*	-6	-4.0/-6.0	800	850	0.4	0.3	4	1
* 3N 180	-40	-45	-40	100	-0.3	-0.3*	-6	-3.0/-6.0	900	850	0.45	0.4	4	1
* 3N 181	-30	-25	-30	300	-0.3	-0.15*	-70	-3.0/-4.0	35	12,500	12.0	6.5	4	1
* 3N 182	-30	-25	-30	300	-1.0	-0.2*	-55	-2.5/-5.0	40	10,000	12.0	7.0	4	1
* 3N 183	-25	-25	-25	300	-2.0	-0.3*	-40	-2.0/-6.0	50	9,000	15.0	10.0	4	1
* 3N 184	-35	-35	-35	300	-0.5	-0.05*	-30	-2.0/-3.0	80	3,500	7.0	3.0	4	1
* 3N 185	-30	-30	-30	300	-1.0	-0.1*	-20	-1.5/-3.0	125	3,000	8.0	4.0	4	1
* 3N 186	-25	-25	-25	300	-2.0	-0.2*	-15	-1.0/-3.5	150	2,800	8.0	4.0	4	1
* 3N 218	-25	-25	-25	300	-0.1	-0.2*	-200	-1.0/-3.5	-15	15,000	45.0	15.0	4	1

CHIPS: All MOS & C/MOS products listed in this catalog are available in chip form.

\* Diode Protected Gate.  
\* Grille protégée par diode.  
\* Gate mit Diode geschützt.

# Preferred type. Available from stock.

# Type preferable. Disponible au magasin.

# Vorzugstyp. Ab Lager lieferbar.